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November 2013

FGH40N60SMDF 600 V, 40 A Field Stop IGBT

Features

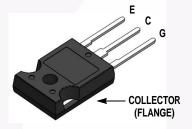
- Maximum Junction Temperature : T_J = 175°C
- Positive Temperaure Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: V_{CE(sat)} = 1.9 V(Typ.) @ I_C = 40 A
- · High Input Impedance
- Fast Switching: E_{OFF} = 6.5 uJ/A
- · Tightened Parameter Distribution
- · RoHS Compliant

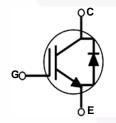
Applications

• Solar Inverter, UPS, Welder, PFC, Telecom, ESS

General Description

Using Novel Field Stop IGBT Technology, Fairchild's new series of field stop 2nd generation IGBTs offer the optimum performance for solar inverter, UPS, welder, telecom, ESS and PFC applications where low conduction and switching losses are essential.





Absolute Maximum Ratings

Symbol	Description		Ratings	Unit	
V _{CES}	Collector to Emitter Voltage		600	V	
V _{GES}	Gate to Emitter Voltage		± 20	V	
I _C	Collector Current	$@ T_C = 25^{\circ}C$	80	А	
.0	Collector Current	@ T _C = 100°C	40	A	
I _{CM (1)}	Pulsed Collector Current @ T _C = 25°C		120	A	
P _D	Maximum Power Dissipation	$ T_C = 25^{\circ}C $	349	W	
	Maximum Power Dissipation	$@ T_C = 100^{\circ}C$	174	W	
T _J	Operating Junction Temperature		-55 to +175	°C	
T _{stg}	Storage Temperature Range		-55 to +175	°C	
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C	

Notes:

1: Repetitive rating: Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction to Case	-	0.43	°C/W
$R_{\theta JC}(Diode)$	Thermal Resistance, Junction to Case	-	1.45	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	40	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGH40N60SMDF	FGH40N60SMDF	TO-247	Tube	N/A	N/A	30

Electrical Characteristics of the IGBT $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
BV _{CES}	Collector to Emitter Breakdown Voltage	$V_{GE} = 0 \text{ V}, I_{C} = 250 \mu\text{A}$	600	-	-	V
$\frac{\Delta BV_{CES}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0 \text{ V, } I_{C} = 250 \mu\text{A}$	-	0.6	-	V/°C
I _{CES}	Collector Cut-Off Current	V _{CE} = V _{CES} , V _{GE} = 0 V	-	-	250	μА
I _{GES}	G-E Leakage Current	$V_{GE} = V_{GES}$, $V_{CE} = 0 V$	-	-	±400	nA
On Charac	teristics					
V _{GE(th)}	G-E Threshold Voltage	$I_C = 250 \mu A, V_{CE} = V_{GE}$	3.5	4.6	6.0	V
GE(III)		I _C = 40 A, V _{GE} = 15 V	_	1.9	2.5	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 40 A, V _{GE} = 15 V, T _C = 150°C	-	2.1	-	V
Dynamic C	haracteristics				1	
C _{ies}	Input Capacitance		-	1880	-	pF
C _{oes}	Output Capacitance	$V_{CE} = 30 \text{ V}, V_{GE} = 0 \text{ V},$ f = 1 MHz	-	180	-	pF
C _{res}	Reverse Transfer Capacitance	- 1 = 1 IVII IZ	-	50	-	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time		-	12	_	ns
t _r	Rise Time		-	20	-	ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 400 \text{ V}, I_{C} = 40 \text{ A},$	-	92	-	ns
t _f	Fall Time	$R_G = 6 \Omega$, $V_{GE} = 15 V$, Inductive Load, $T_C = 25^{\circ}C$	-	13	20	ns
E _{on}	Turn-On Switching Loss		-	1.3	-	mJ
E _{off}	Turn-Off Switching Loss		-	0.26	-	mJ
E _{ts}	Total Switching Loss		-	1.56	-	mJ
t _{d(on)}	Turn-On Delay Time		_	12	- /	ns
t _r	Rise Time		-	19	- /	ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 400 \text{ V}, I_{C} = 40 \text{ A},$	-	97	-	ns
t _f	Fall Time	$R_G = 6 \Omega$, $V_{GE} = 15 V$,	-	14	21	ns
E _{on}	Turn-On Switching Loss	Inductive Load, T _C = 150°C	-	2.09	- /	mJ
E _{off}	Turn-Off Switching Loss		-	0.44	- (mJ
E _{ts}	Total Switching Loss		-	2.53	- \	mJ
Qg	Total Gate Charge		-	119	-	nC
Q _{ge}	Gate to Emitter Charge	$V_{CE} = 400 \text{ V}, I_{C} = 40 \text{ A},$ $V_{GF} = 15 \text{ V}$	-	13	-	nC
Q _{gc}	Gate to Collector Charge	▼GE - 13 V	-	58	-	nC

Electrical Characteristics of the Diode $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Тур.	Max	Unit
V _{FM}	Diode Forward Voltage	I _E = 20 A	$T_C = 25^{\circ}C$	-	1.3	1.7	V
	2.000 r ormana romage		$T_{\rm C} = 150^{\rm o}{\rm C}$	°C - 1.2			
t _{rr} Diode Reverse Recovery Ti Q _{rr} Diode Reverse Recovery Ci	Diode Reverse Recovery Time		$T_C = 25^{\circ}C$	-	70	90	ns
	2.000 1.010.00 1.00010.9 1	I _F =20 A, di _F /dt = 200 A/μs	$T_{\rm C} = 150^{\rm o}{\rm C}$	-	126		
	Diode Reverse Recovery Charge	η -20 / 1, αιρ/αι - 200 / 1 μο	$T_C = 25^{\circ}C$	-	207	290	nC
	2 iodo riororos riocorory circai go		$T_{\rm C} = 150^{\rm o}{\rm C}$	0°C - 638			

Figure 1. Typical Output Characteristics

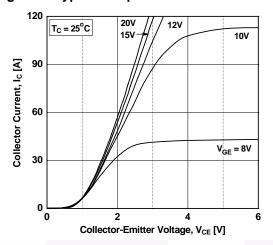


Figure 3. Typical Saturation Voltage Characteristics

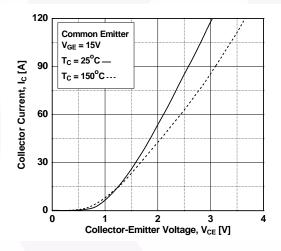


Figure 5. Saturation Voltage vs. Case
Temperature at Variant Current Level

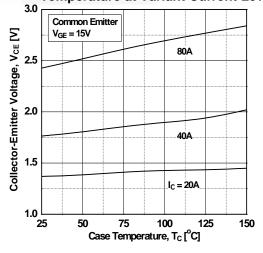


Figure 2. Typical Output Characteristics

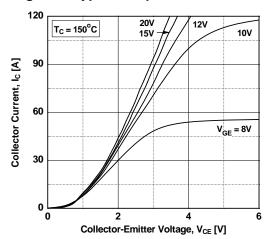


Figure 4. Transfer Characteristics

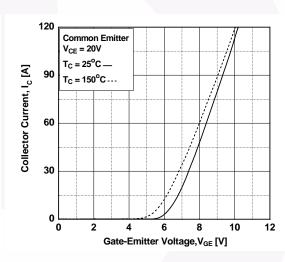


Figure 6. Saturation Voltage vs. V_{GE}

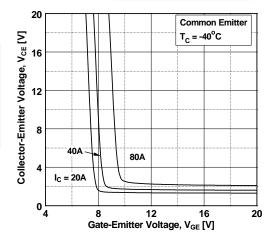


Figure 7. Saturation Voltage vs. V_{GE}

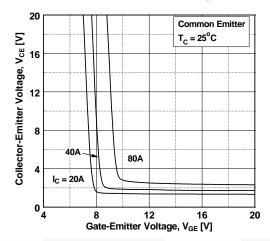


Figure 8. Saturation Voltage vs. V_{GE}

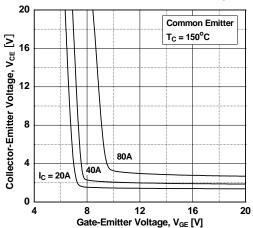


Figure 9. Capacitance Characteristics

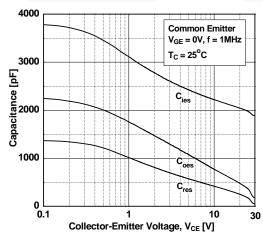


Figure 10. Gate charge Characteristics

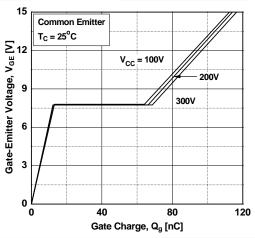


Figure 11. SOA Characteristics

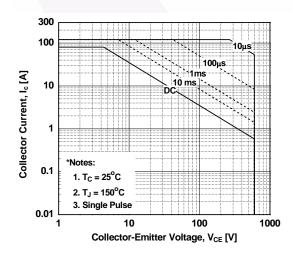


Figure 12. Turn-on Characteristics vs.
Gate Resistance

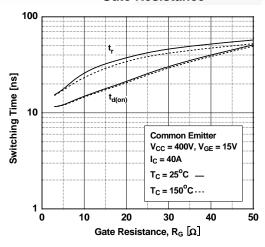


Figure 13. Turn-off Characteristics vs.
Gate Resistance

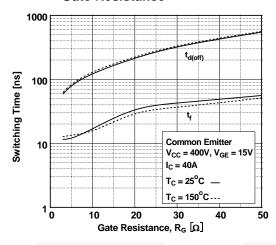


Figure 14. Turn-on Characteristics vs.
Collector Current

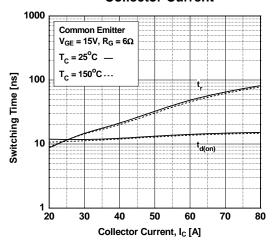


Figure 15. Turn-off Characteristics vs. Collector Current

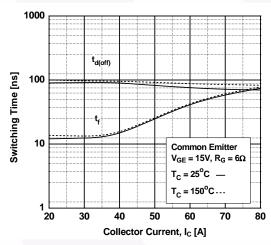


Figure 16. Switching Loss vs.
Gate Resistance

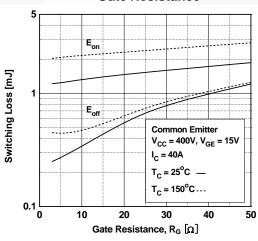


Figure 17. Switching Loss vs. Collector Current

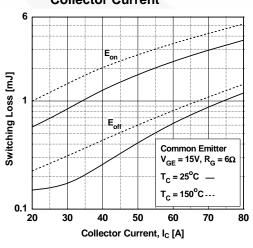


Figure 18. Turn off Switching SOA Characteristics

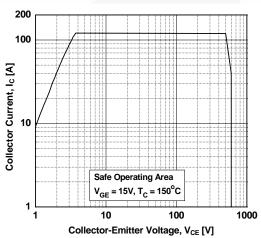


Figure 19. Forward Characteristics

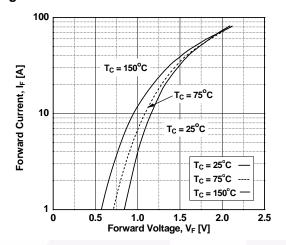


Figure 20. Reverse Current

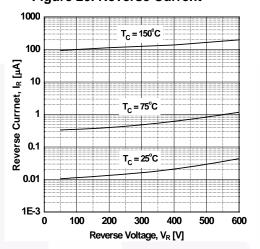


Figure 21. Stored Charge

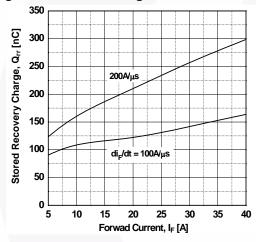


Figure 22. Reverse Recovery Time

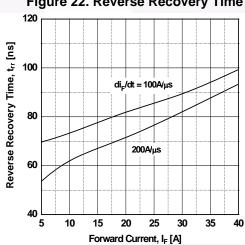
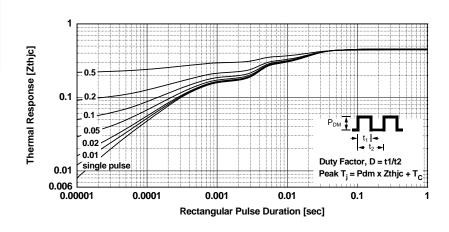


Figure 23. Transient Thermal Impedance of IGBT



Mechanical Dimensions В 15.87 E φ^{3.65}/_{3.51}/_E Φ 0.254 Μ Β ΑΜ 12.81 E $\phi_{3.51}^{3.65}$ 5.58 E 1.35 Ø 5.20 F 13.08 MIN 3 16.25 E (1.60) 3 2.66 5.56 11.12 NOTES: UNLESS OTHERWISE SPECIFIED. A. PACKAGE REFERENCE: JEDEC TO-247, ISSUE E, VARIATION AB, DATED JUNE, 2004. B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS. ALL DIMENSIONS ARE IN MILLIMETERS. D. DRAWING CONFORMS TO ASME Y14.5 - 1994 DOES NOT COMPLY JEDEC STANDARD VALUE NOTCH MAY BE SQUARE

Figure 24. TO-247 3L - TO-247, MOLDED, 3 LEAD, JEDEC VARIATION AB

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